

#### DEVELOPMENT OF MATERIALS PROCESSING METHODS:

#### CATHODIC VACUUM ARC AND PLASMA IMMERSION ION IMPLANTATION COMBINED

**Marcela Bilek** 

Applied & Plasma Physics Group, School of Physics, University of Sydney



### **Requirements for Advanced Coatings**

- No voids
- No cracking or resistance to crack propagation
- No delamination
- For some applications we need
  - Enhanced hardness
  - Enhanced toughness
  - Enhanced biocompatibility



# **Energetics of Delamination**

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 Griffith Criterion for crack propagation or delamination: If the strain energy relieved exceeds the energy required to create the two new surfaces a film will delaminate, once a nucleation point has formed





**Our Strategies** 

- Low stress and substrate mixing layers for super adhesion
- Nanostructuring for enhanced hardness, resistance to cracking and supertoughness



- Low -> voids (tensile stress)
- Intermediate -> dense, well connected (compressive stress)
- High -> observations show reduced stress and interface mixing





### **Stress Generated by Ion Impacts**

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• Observed universal behaviour as a function of energy



High energy impacts can relieve the stress generated by lower energy impacts



### The Universal Curve for AlN

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# **The Cathodic Vacuum Arc**

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• Discharge triggered by direct contact or surface flashover



- Plasma drifts away normal to cathode surface
- FULLY ionized & energetic (10-100s of eV)





few hundred microns









### **Cathodic Arc Treatment of Cutting Tools**

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Protective coatings for cutting tools produced using unfiltered arcs

Ti cathodes in nitrogen





Chromium cathodes in argon (etch) Photographs courtesy of Sutton Tools



### **Magnetic Filter**

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- Curved solenoid used to guide plasma around bend while macro-particles go straight ahead
- Use arc current to establish magnetic field (~10-100 mT)



• Electrons magnetized & ions follow by electrostatic attraction

Andre Anders & Othon R. Monteiro Lawrence Berkeley National Laboratory California USA



Plasma Immersion Ion Implantation (PIII)

- Bias applied to workpiece immersed in plasma (~10 kV)
- Arrows show electric field and direction of implanting ions
- Condensable plasma = bombardment during film growth
- Non-condensable plasma = subsurface implantation



### **PIII&D Filtered Cathodic Arc System**





## The PIII&D Process

97.5 - 99.6 % of cycle School of Physics, University of Sydney

2.5 - 0.4 % of cycle





Cathodic arc deposition

1700 -20,000 eV



PIII (20 µs, 200-1250 Hz)



#### **Stress versus implantation energy**

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• stress versus high voltage bias energy for 20  $\mu$ s applied at three different pulsing frequencies during the deposition of carbon films.





#### **Macroscopic Stress Relief**

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  On a macroscopic scale, the film stress will be reduced as more of the film's volume is subjected to the high-energy thermal spikes
- Volume treated is proportional to *Ef* (or *Vf*)

relief to 0.75 GPa occurs around  $Vf \sim 2000$  kV.Hz.

Can be achieved with pulses of: 10 kV @ 200 Hz 2.5 keV @ 800 Hz 1.7 kV @ 1200 Hz





#### The Vf relation in AlN

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• PIII during deposition for bias voltages between 0.1 and 6.4 kV and frequencies ranging from 20 to 2000 Hz





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 Data from titanium nitride films produced with PIII&D using energies of 5 and 15 kV and pulsing frequencies of 100 Hz, 500 Hz and 1200 Hz (20 µs pulse length as before)





### **Stabilization of Metastable Phases**

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#### Structure of Boron Nitride





(b) Cubic Boron Nitride

replacing carbon atoms in diamond.

(a) Hexagonal Boron Nitride Layers where nitrogen and boron atoms combined in a hexagonal network are superimposed and have a structure similar to graphite.

B. Abendroth, R. Gago, A. Kolitsch, W. Möller, Institute of Ion Beam Physics and Materials Research, Forschungszentrum Rossendorf e.V., Dresden Germany





# **Remaining Challenges**

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• Uniform treatment of **complex shapes** avoiding breakdown

# Treating insulating materials ↓

# **SHEATH DYNAMICS**

## Practical Surfaces: Complex shapes





### **Sheath Dynamics**

- Ion focusing occurs near tips increasing dose
- Small sheath width increases breakdown risk





# **Equilibrium Sheath**



- PIC code to simulate sheath evolution in drifting plasma
- (a) Flat substrate
- (b) 30° cone
- (c) 60° cone
- (d) 90° cone



# **Dose Effects**

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#### Implantation phase

Deposition phase









# **Insulators: Charging Effects**

- Surface charging results in voltage droop (lower energy)
- Time for sheath to collapse down to 5 mm at an applied bias of 5 kV as measured by a Langmuir probe.





# **Solutions under study**

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• Thin conductive and ion transparent coatings stripped after treatment

• Ion implantation through mesh



### Structure at the nanoscale

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#### **Cross-section view of Abalone Shell**

#### The structure of an abalone shell

Figures 1a and 1b: SBM Images of cross sections showing layered structure

Figures 2a-e:

2a. TBM image shows organic layer between platelets







2b,c. Diffraction patterns showing orientations of platelets

2d. Interface between organic and inorganic layers

2e. Interface between two platelets of aragonite

http://www.princeton.edu/~pmi/REU/presentations



### A Multilayered Structure





### **Crack Propagation**

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A crack propagating in a direction perpendicular to the layers is arrested at a soft layer since stress concentrated at the crack tip is reduced (*Okumura and de Gennes, European Physical Journal E, vol 4, p121, 2001*)



The Multilayer Advantage

- Increased fracture toughness
- possible mechanism
  - Arresting of cracks at interfaces





# **Surface Relaxation Method**

- 11.4 micron carbon film grown in the vacuum arc
- About 200 layers
- Dark layers result from surface relaxation when PIII&D stopped





#### Pin-on-disc wear tester + impact system





#### Combined wear test with Impacts

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• 50 N impacts every 10 sec,  $\approx 8.5 \text{ sec} (a) 1 \text{ N}$ , 1 sec (a) 0 N

• Disk at constant 2000 rpm rotation in Haemaccel®



#### Ti6Al4V pin on 2 $\mu m$ thick (48 nm layers) carbon disc

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Ti6Al4V pin on 2  $\mu$ m thick carbon disc: Wear + Impact

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Carbon (48 nm layers)



Ti6Al4V pin

20 mm

6 mm

Pin and disc pair after 20 minutes wear + impact testing @ 2000 rpm

120 impacts @ 50 N

The disc has worn through to the metal, and the pin shows substantial wear



#### Ti6Al4V pin on carbon disc: Wear + Impact

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Pin and disc pair after 20 minutes wear + impact testing @ 2000 rpm

120 impacts @ 50 N

Visual inspection of disc suggests mostly asperity wear, with little erosion into the bulk of the coating

Ti6Al4V pin



#### **Performance Enhancements by Multilayering**

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#### Layer Thickeness (nm)

- Graph shows wear and impact time to failure for multilayered carbon films, 2 µm thick, on Ti6Al4V
- Interruptions to deposition produce a relaxed layers of higher density
- "Supertoughness" effect at optimum bilayer period

### Nanoscale Multilayers:

Time variations in condensing species and surface mobility

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- Multilayered coatings
- 17 nm bilayer period





(a) TEM image (the scale bar represents 100 nm);

(b) shows a nitrogen elemental map from the same region.



### Multilayer in the Ti/TiN System

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- Produced using cathodic vacuum arc PVD
- Ti provides a soft layer between alternate layers of TiN
- 17 nm bilayer period



BF image

#### Ti EELS map

#### N EELS map



### Limitations of Single Source dc Vacuum Arc

- single source limits the range of composition of constituent layers
- density of the dc plasma plume fluctuates strongly with the instantaneous arc current  $\Rightarrow$  deposition of precise layer thicknesses at the nanoscale difficult



- new system with two sources pulsed
- pulsed sources deliver known current per pulse (easy to calibrate)
- lower macroparticle production in pulsed mode  $(I\uparrow)$
- currents of 1-5 kA ensures competitive rates



# New System Design





# **Source Design**

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•based on design of Siemroth et al, Surface and Coatings Technology, 68/69, 314-319, 1994



### Centre trigger for uniform erosion





Cathode spots

- Current is conducted through µm diameter spots on cathode surface
- Current limited to ~ 100A per spot. Arcs >100A exhibit multiple spots.
- Current density extremely high.  $10^9 10^{12}$  A. m<sup>-2</sup>
- ~ 90% of plasma flux is electrons,~10% metal ions



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Retrograde Motion.

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- In an external magnetic field, parallel to cathode surface, spots move in -J x B direction.
- In high current arcs with multiple spots, retrograde motion acts to repel spots away from one another.





### **1 ms exposures of cathode spots**

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200µs

400µs Image size 50mm square

#### Cathode and anode currents

50 mm diameter Titanium cathode

177 mm diam. circular Al substrate biased at -90 V

Filter duct: Initial field 43mT Bias +35 V



#### Rogowski coil positions





#### Falling axial duct field during pulse

177 mm diameter circular Al substrate biased at -90 V

Filter duct fields need to be matched to the plasma flux

Field triggered <u>before</u> cathode







#### Ion and electron currents, measured at substrate







#### Plasma current $(I_{p})$ along filter duct- four Rogowskis

50 mm diam. Ti cathode 177 mm diam. circular Al substrate biased at +90 V

Filter duct Initial field 43mT Bias: +35 V





#### Substrate bias affects plasma current $(I_p)$ in exit Rog

50 mm diam. Ti cathode 177 mm diam. circular Al substrate biases:

+90 V, Earth, Float, -90 V

Filter duct Initial field 43mT Bias: +35 V









# Conclusions

- Equivalence of the voltage and pulse frequency for achieving stress relief ⇒ substitution of low bias with higher rep rates for high bias with low rep rates
  - 20 kV for 20  $\mu$ s @ 200 Hz = 4 kV for 20  $\mu$ s @ 1000 Hz
- Minimising the voltage requirements for feed-throughs and the potential for arcing (breakdown) on the substrates is useful for the coating of objects with complex shapes and sharp edges
- Superior performance can be achieved by nanostructured coatings such as nanoscale multilayers
- High current dual source pulsed arc system constructed
- High current fast moving spots reduce macroparticle emission
- Open filter to efficiently remove residual macroparticles
- Centre trigger ensures deposition rate stability over time



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- Achieved deposition rates of around 0.25 nm per pulse = few tens of pulses per layer for nanolayered materials
- Pulses must be repeatable in composition and amount of material ejected (type 2 spots must be ensured)
  - cathode must always be properly conditioned
  - adsorption of gases between pulses must be controlled
  - linked to pressure when using background gas

### Centre trigger for uniform erosion



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The key to a time stable deposition rate





Spot Types

- Contamination of cathode surface leads to variation in spot parameters.
- Type I spots: short lifetime, high velocity and small current per spot. Associated with surface contaminants
- Type II spots: longer lifetime, lower velocity and large current per spot. Associated with clean cathode surface.



# **Type 1 and 2 spot behaviours**

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 In the deposition of multilayered films it will be important to ensure that only type 2 spots contribute to the plasma reaching the substrate
 pulse # increasing



(a) type 1 arc - exp 100 $\mu$ s (b) type 1 and 2 arcs exp - 500  $\mu$ s (c) type 2 arc - exp 2000 $\mu$ s Al cathode. The power supply was the simple 12mF capacitor bank charged to 110V.

Notes: Anode spot in (a); Type 2 (brighter, slower moving) occasionally nucleate due to uneven cathode erosion



#### **Measuring Stress**

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Wafer curvature with profilometer & Stoney's Equation

where: 
$$\sigma = \frac{1}{6} \bullet \left[ \frac{1}{R_f} - \frac{1}{R_s} \right] \bullet \frac{E}{(1 - \nu)} \bullet \frac{t_s^2}{t_f}$$

W

= stress in film after deposition σ

- $R_{f}$  = substrate radius of curvature post deposition
- substrate radius of curvature pre deposition  $R_{c} =$

$$E = Young's modulus$$

$$v = Poisson's ratio$$

$$t_s =$$
 substrate thickness

$$t_f = film thickness$$

Proc. R. Soc., 1909

\* 300 micron Si wafer and film grown to ~10 microns



- First try (a) simple capacitor bank of between 6 and 12 mF, charged to between 100 and 400V
- Later (b) based on oscillating LC circuit used by Siemroth et al, adapted for electrolytic capacitors (for pulse shape control)





#### **Current Profiles**

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- (a) simple 12mF, 400V capacitor bank
- (b) 300V LC pulse circuit, crowbarred at 1ms

Rising current pulse profile has much better cathode erosion characteristic





#### **Design Issues**

- Peak ion current balance good magnetic confinement and fewer macroparticles with too much force on filter coil and losses scaling as I<sup>2</sup> (we chose 1-5 kA operation – CSD??)
- Pulse length is dictated by the radius of the cathode and the velocity of the cathode spots (metals 0.5 ms @ 3.5 kA peak I and reduce size of graphite target as would need 2 ms)
- Limits on pulse frequency set by tolerance of circuit components to heating. Designed for 10 Hz maximum pulsing frequency but may not be possible to achieve at high end of current range
- With a given L and C (resonant frequency) we adjust the charge voltage to vary peak I and crowbar time to vary pulse length
- This prototype dissipated only 400 W when running at maximum capacity of the wiring



#### **Optimising for Cathode Erosion**

- School of Physics, University of SydneyHigh speed CCD camera focused on carbon cathode
- Both charged to 300V, (b) crowbarred at 1ms





Current profile (a) -2 ms exp. Current profile (b) -1 ms exp.\* complicated interplay between the current and the inter-spot distance



#### Faster type 1 to 2 transition with LC Resonator Supply

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• occurrs within a few arc pulses





# Conclusions

- Design of dual source pulsed filtered cathodic arc for multilayer coatings constructed further optimisation needed
- Important characteristics and operating parameters are:
  - time dependence of the arc current pulse is important in giving even erosion & sharp type 1 –2 transition
  - controlled rates of nonreactive deposition in vacuum due to the reproducible arc current pulse profile
  - controlled rates of deposition and controlled stoichiometry should also be achievable during reactive deposition processes when a background gas is used – need to balance pressure and rep. rate
- Effect of arc current and background gas pressure on the charge state distribution (CSD) of the plasma ions should be monitored to understand how the impact energy of ions will be affected by substrate bias